# 2SC5846G

### Silicon NPN epitaxial planar type

For general amplification

#### Features

- High forward current transfer ratio  $h_{FE}$
- SSS-mini type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V					
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V					
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	7	V					
Collector current	I <sub>C</sub>	100	mA					
Peak collector current	I <sub>CP</sub>	200	mA					
Collector power dissipation	P <sub>C</sub>	100	mW					
Junction temperature	Tj	125	°C					
Storage temperature	T <sub>stg</sub>	-55 to +125	°C					

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

#### Package

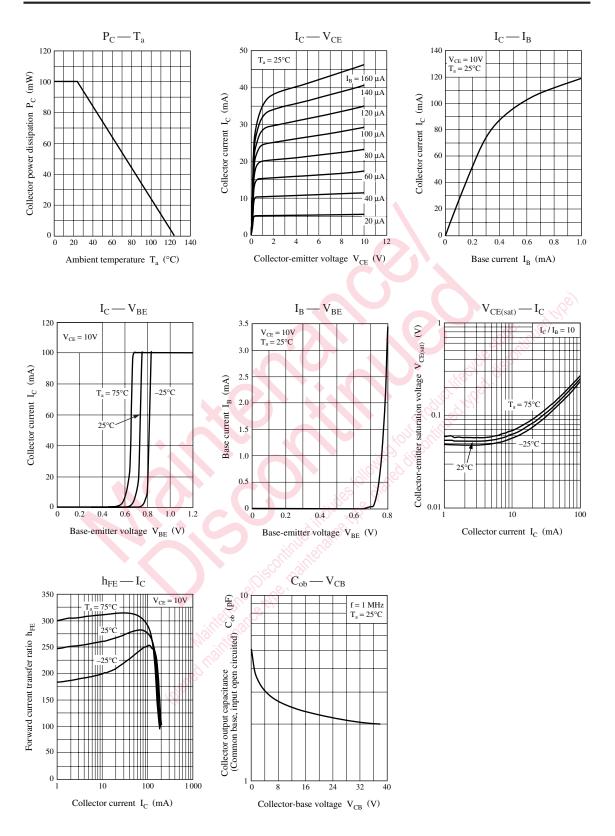
- Code
  - SSSMini3-F2
- Marking Symbol: 7K
- Pin Name
  - 1. Base
  - 2. Emitter
  - 3. Collector

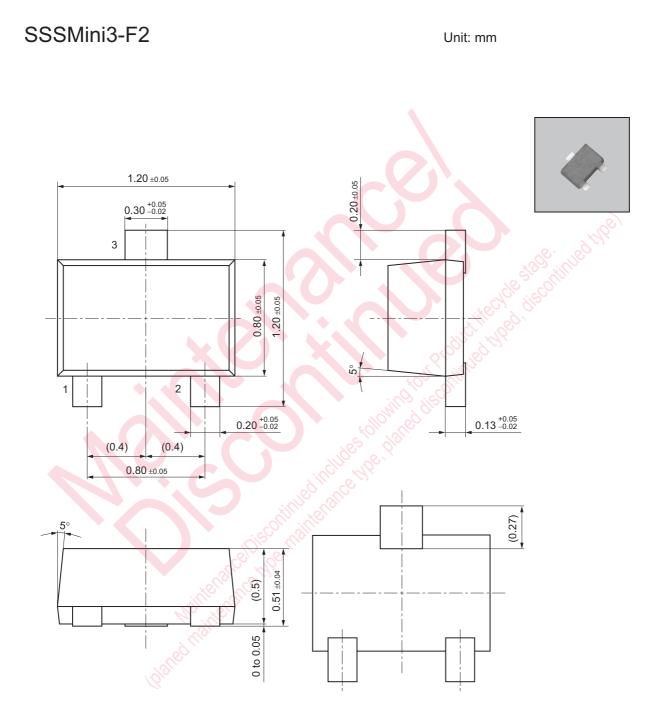
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2  {\rm mA},  I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	7			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	180		390	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.1	0.3	V
Collector output capacitance (Common base, input open circuited)	Cob	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$		2.2		pF
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		100		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## Panasonic





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